

## PNP SILICON TRANSISTOR

## **FEATURES**

Power dissipation

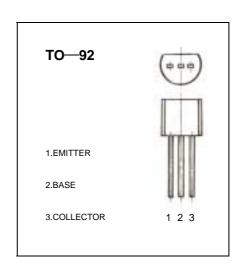
 $P_{\text{CM}}$  : 0.625 W (Tamb=25°C)

Collector current

 $I_{CM}$  : -0.5

Collector-base voltage

 $V_{(BR)CBO}$ : -40



## **ELECTRICAL CHARACTERISTICS (Tamb=25℃** unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	Ic= -100 μ A, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	Ic= -0. 1 mA, I <sub>B</sub> =0	-20			V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> = -100 μ A, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-40 V I <sub>E</sub> =0			-0.1	μА
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =- 20 V I <sub>B</sub> =0			-0.2	μА
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = - 5 V, I <sub>C</sub> =0			-0.1	μА
DC current gain(note)	H <sub>FE (1)</sub>	$V_{CE} = -1$ V, $I_{C} = -50$ mA	64		300	
DC current gain(note)	H <sub>FE (2)</sub>	$V_{CE} = -1V$ , $I_{C} = -500 \text{ mA}$	40			
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50 mA			-0.6	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =-500mA,I <sub>B</sub> =-50 mA			-1.2	V
Base-emitter voltage	V <sub>EB</sub>	I <sub>E</sub> =-100mA			-1.4	V
Transition frequency	f <sub>τ</sub>	$V_{CE}$ =- 6 V, $I_{C}$ = -20 mA $f$ =30MHz	150			MHz

CLASSIFICATION OF H<sub>FE(1)</sub>

Rank	D	Е	F	G	Н	I
Range	64-91	78-112	96-135	112-166	144-202	190-300

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